



STL7NM60N

N-channel 600 V, 0.805 Ω , 5.8 A PowerFLAT™ 5x5
MDmesh™ II Power MOSFET

Features

Order code	V _{DSS} @ T _{JMAX}	R _{DS(on)} max.	I _D
STL7NM60N	650 V	< 0.90 Ω	5.8 A ⁽¹⁾

1. The value is rated according Rthj-case

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

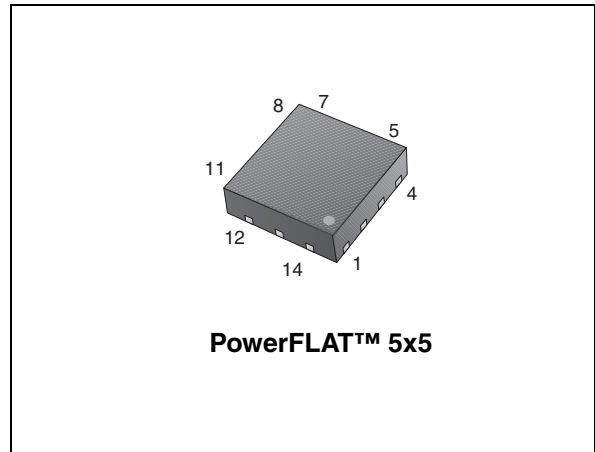


Figure 1. Internal schematic diagram

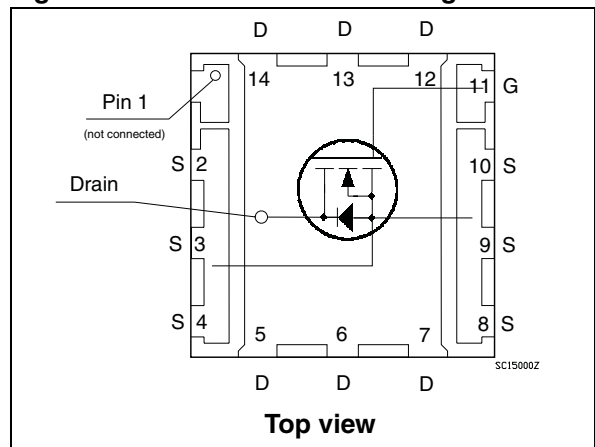


Table 1. Device summary

Order code	Marking	Package	Packaging
STL7NM60N	7NM60N	PowerFLAT™ 5x5	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5.8	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.7	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb} = 25\text{ }^\circ\text{C}$	1.4	A
$I_D^{(2)}$	Drain current (continuous) at $T_{amb} = 100\text{ }^\circ\text{C}$	0.9	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	5.6	A
$P_{TOT}^{(2)}$	Total dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	4	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	68	W
I_{AS}	Avalanche current, repetitive or not-repetitive ⁽³⁾	2	A
E_{AS}	Single pulse avalanche energy ⁽⁴⁾	119	mJ
$dv/dt^{(5)}$	Peak diode recovery voltage slope	15	V/ns
T_J T_{stg}	Operating junction temperature storage temperature	-55 to 150	$^\circ\text{C}$

1. The value is rated according $R_{thj-case}$.
2. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$
3. Pulse width limited by T_{jmax}
4. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$
5. $I_{SD} \leq 5.8\text{ A}$, $dv/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	1.85	$^\circ\text{C/W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max.	31.3	$^\circ\text{C/W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$.

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS}=0$)	$I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS}=0$)	$V_{DS} = 600\text{ V}$, $V_{DS} = 600\text{ V}$, $T_c = 125^{\circ}\text{C}$			1 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS}=0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS}=10\text{ V}$, $I_D=2.5\text{ A}$		0.805	0.90	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$, $f=1\text{ MHz}$, $V_{GS}=0$	-	363 24.6 1.1	-	pF pF pF
$C_{oss\text{ eq. (1)}}$	Output equivalent capacitance	$V_{GS}=0$, $V_{DS}=0$ to 480 V	-	130	-	pF
R_g	Gate input resistance	$f=1\text{ MHz}$ gate DC bias=0 test signal level = 20 mV open drain	-	5.4	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD}=480\text{ V}$, $I_D=5\text{ A}$ $V_{GS}=10\text{ V}$ (see Figure 15)	-	14 2.7 2.7	-	nC nC nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}=300\text{ V}$, $I_D=2.5\text{ A}$, $R_G=4.7\text{ }\Omega$, $V_{GS}=10\text{ V}$ (see Figure 14)		7 10 26 12		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		5.8	A
$I_{SDM}^{(1)(2)}$	Source-drain current (pulsed)				23	A
$V_{SD}^{(3)}$	Forward on voltage	$I_{SD} = 5\text{ A}$, $V_{GS} = 0$	-		1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16)	-	213		ns
Q_{rr}	Reverse recovery charge			1.5		nC
I_{RRM}	Reverse recovery current			14		A
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16)	-	265		ns
Q_{rr}	Reverse recovery charge			1.8		nC
I_{RRM}	Reverse recovery current			14		A

1. Pulse width limited by safe operating area.
2. When mounted on FR-4 board of 1inch², 2 oz Cu.
3. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

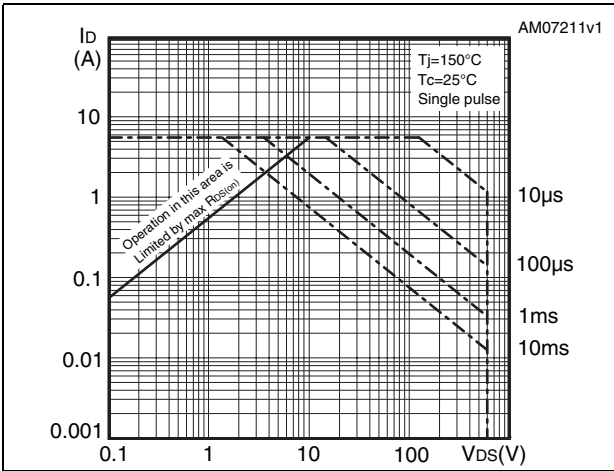


Figure 3. Thermal impedance

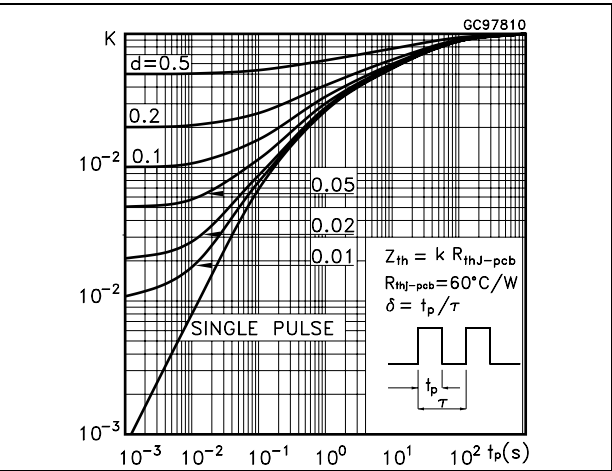


Figure 4. Output characteristics

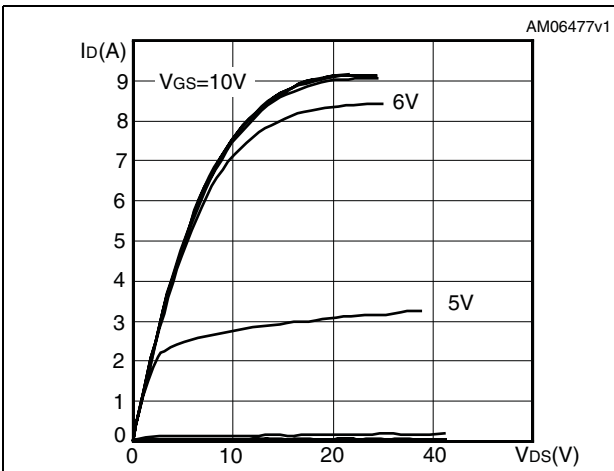


Figure 5. Transfer characteristics

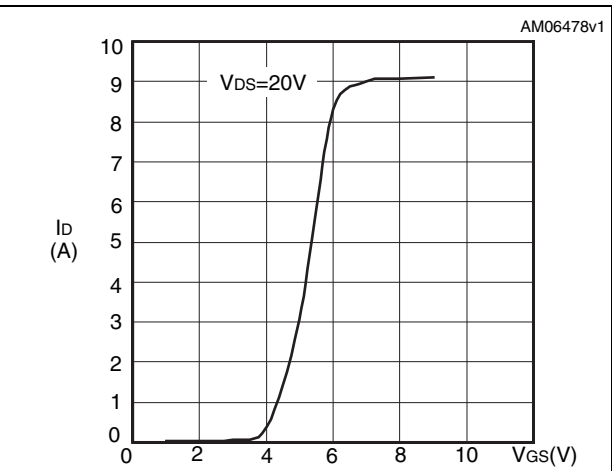


Figure 6. Gate charge vs gate-source voltage

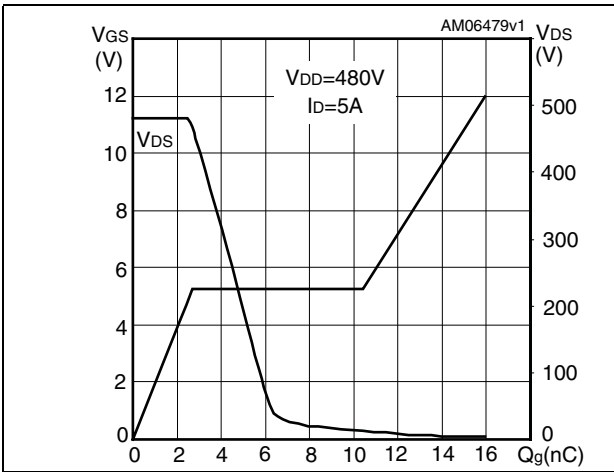


Figure 7. Static drain-source on resistance

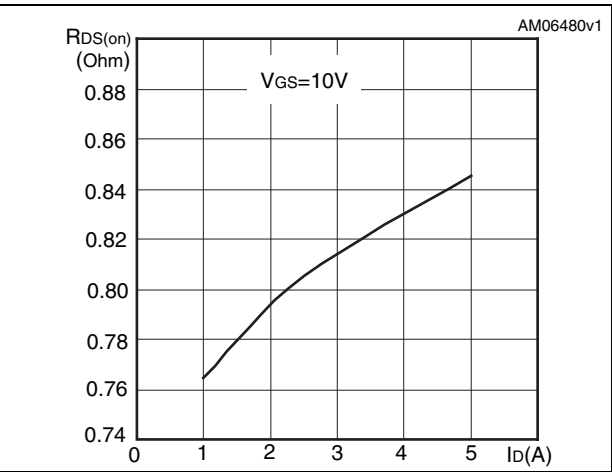


Figure 8. Capacitance variations

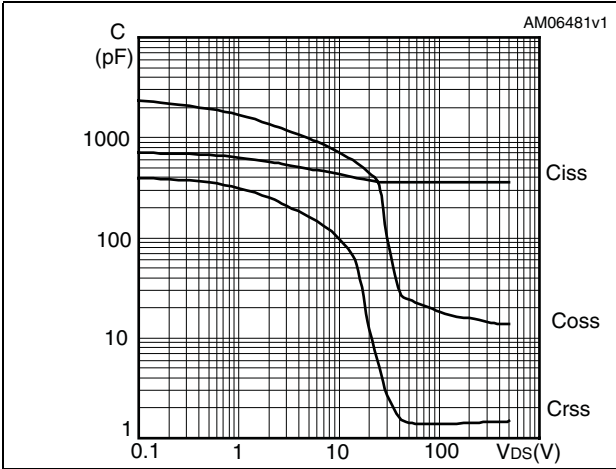


Figure 9. Output capacitance stored energy

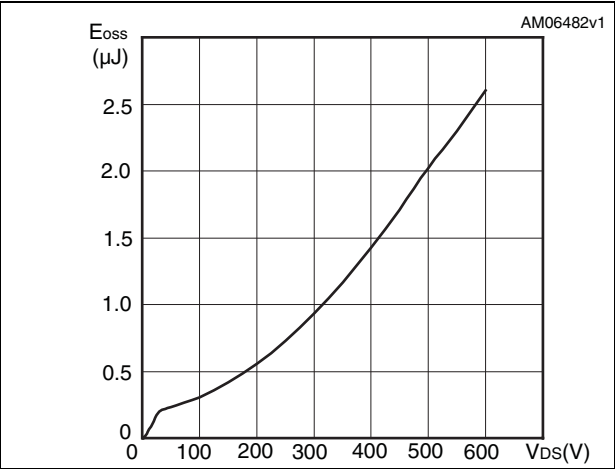


Figure 10. Normalized gate threshold voltage vs temperature

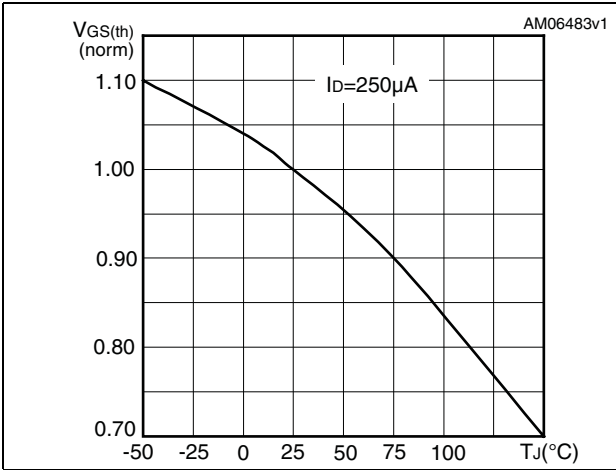


Figure 11. Normalized on resistance vs temperature

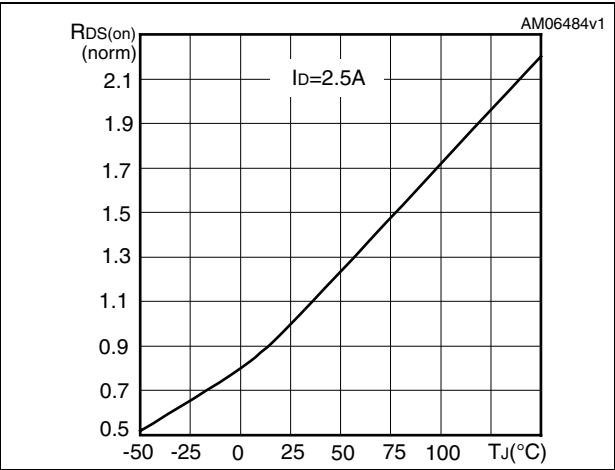


Figure 12. Normalized BVDS vs temperature

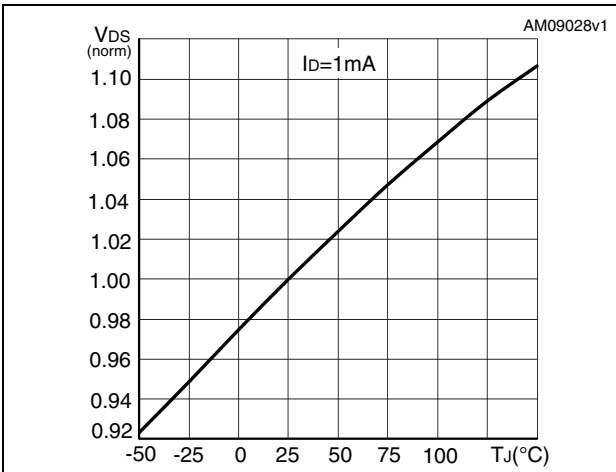
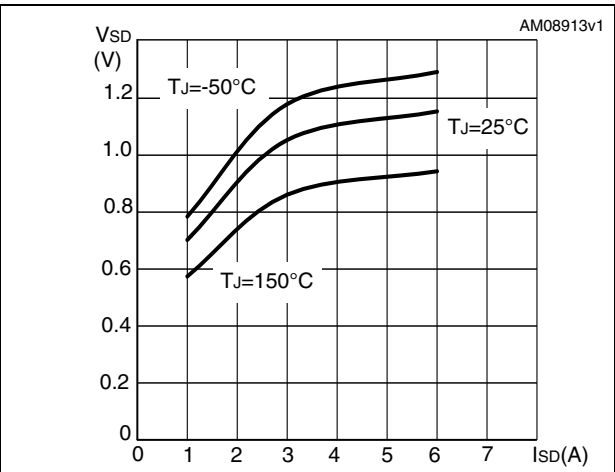


Figure 13. Source-drain diode forward characteristics



3 Test circuits

Figure 14. Switching times test circuit for resistive load



Figure 15. Gate charge test circuit



Figure 16. Test circuit for inductive load switching and diode recovery times

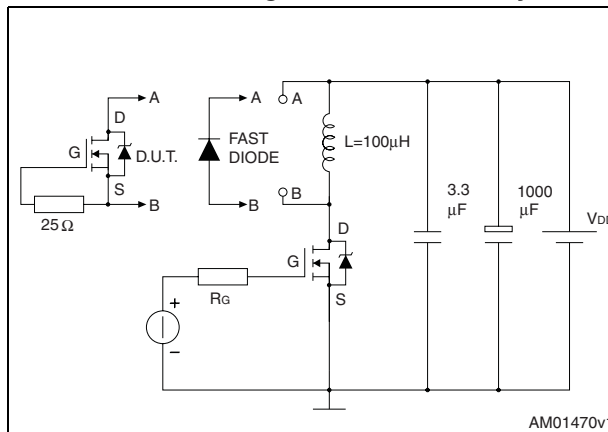


Figure 17. Unclamped inductive load test circuit



Figure 18. Unclamped inductive waveform

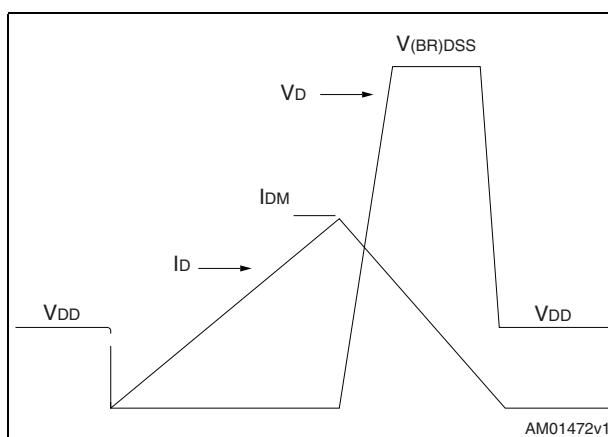
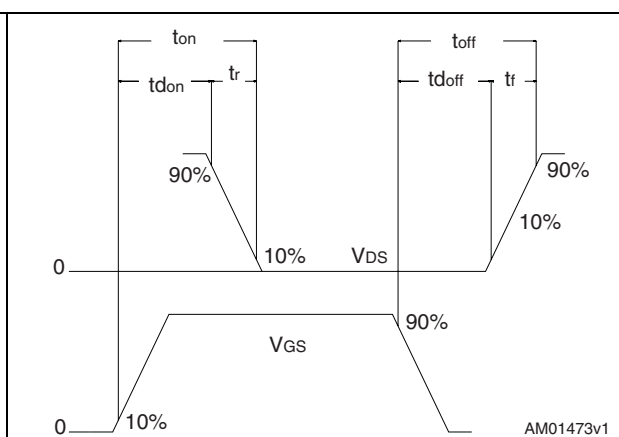


Figure 19. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. PowerFLAT™ 5x5 mechanical dimensions

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.0
A1	0	0.02	0.05
A3		0.24	
D	4.90	5.0	5.10
E	4.90	5.0	5.10
E2	2.49	2.57	2.64
e	1.22	1.27	1.32
b	0.43	0.51	0.58
c	0.64	0.71	0.79

Figure 20. PowerFLAT™ 5x5 mechanical drawing

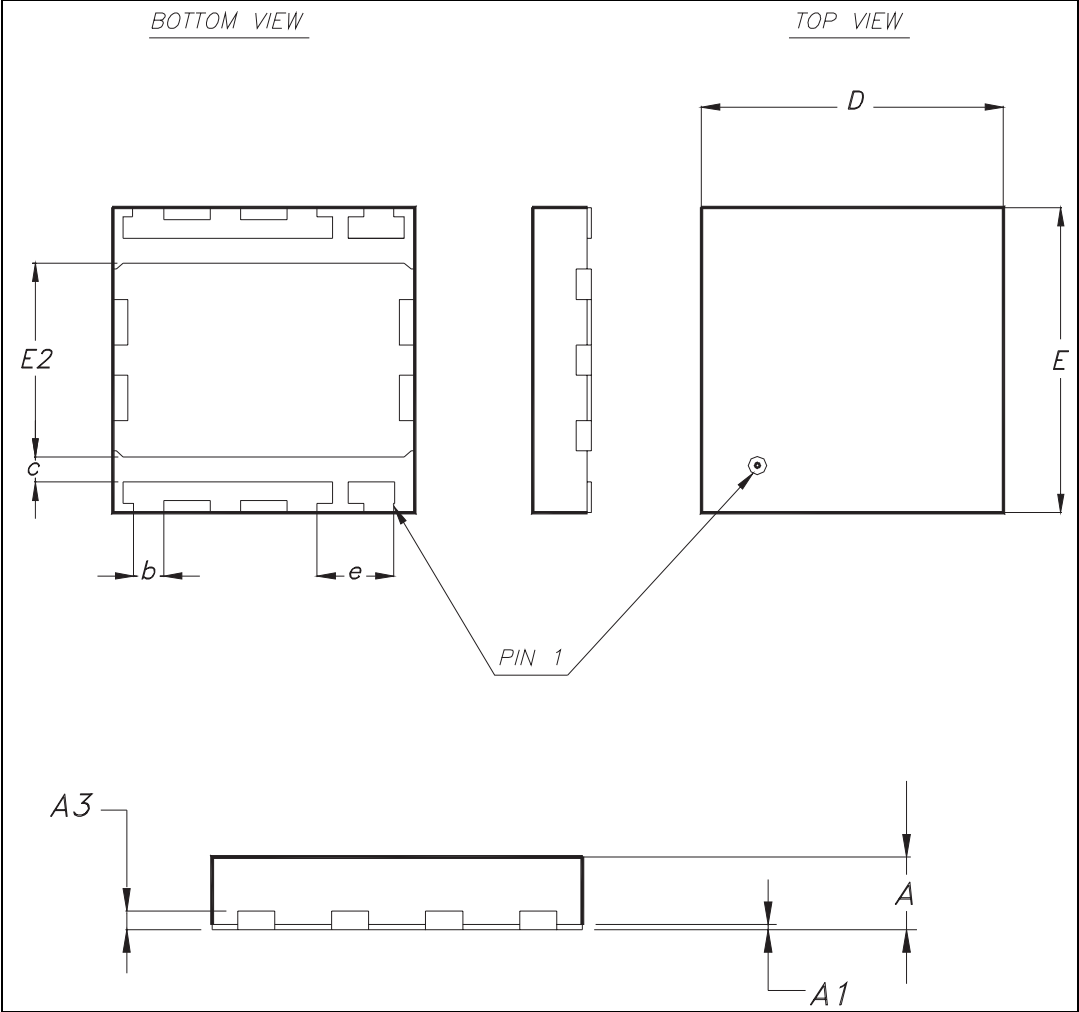
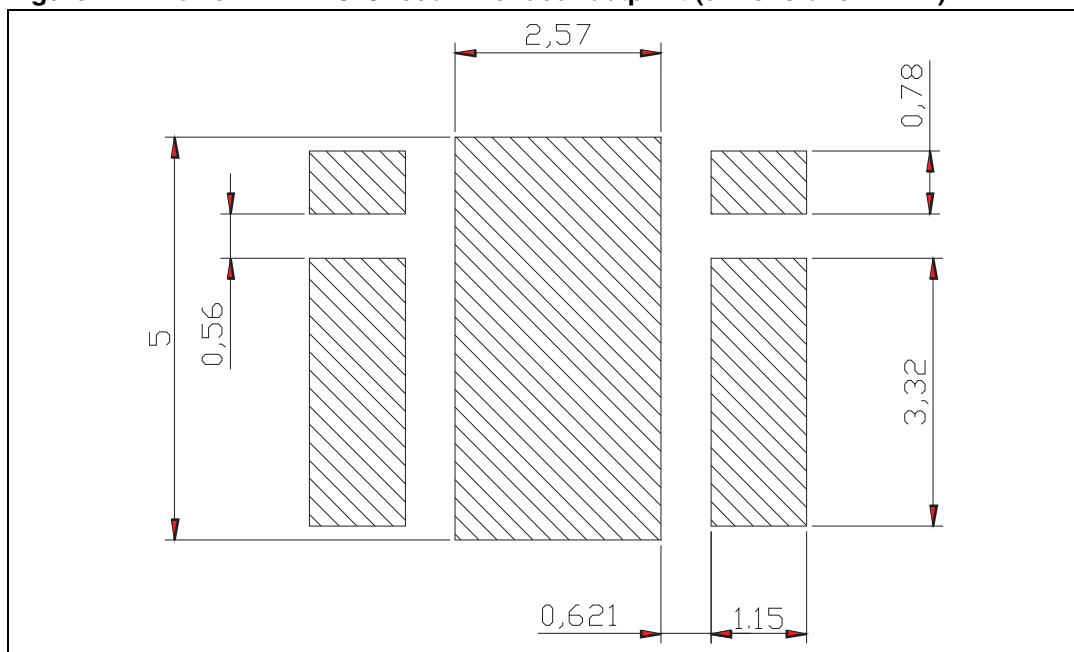


Figure 21. PowerFLAT™ 5x5 recommended footprint (dimensions in mm)

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
18-Jan-2011	1	First release.
10-Nov-2011	2	Updated Figure 1: Internal schematic diagram in cover page. Updated Table 2: Absolute maximum ratings and Section 4: Package mechanical data . Minor text changes.

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